

NCEP85T25D

# NCE N-Channel Super Trench Power MOSFET

#### Description

The NCEP85T25D uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of  $R_{DS(ON)}$  and  $Q_g$ . This device is ideal for high-frequency switching and synchronous rectification.

### **General Features**

- V<sub>DS</sub> =85V,I<sub>D</sub> =250A
  R<sub>DS(ON)</sub> <2.8mΩ @ V<sub>GS</sub>=10V
- Excellent gate charge x R<sub>DS(on)</sub> product
- Very low on-resistance R<sub>DS(on)</sub>
- 175 °C operating temperature
- Pb-free lead plating
- 100% UIS tested

### Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

100% UIS TESTED!

100% ΔVds TESTED!

### **Package Marking and Ordering Information**

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP85T25D	NCEP85T25D	TO-263-2L	-	-	-

### Absolute Maximum Ratings (T<sub>c</sub>=25<sup>°</sup>Cunless otherwise noted)

Absolute Maximum Natings (16-25 Cumess otherwise noted)					
Parameter	Symbol	Limit	Unit		
Drain-Source Voltage	Vds	85	V		
Gate-Source Voltage	Vgs	±20	V		
Drain Current-Continuous	Ι <sub>D</sub>	250	А		
Drain Current-Continuous(T_c=100 $^{\circ}$ C)	I <sub>D</sub> (100℃)	180	А		
Pulsed Drain Current	I <sub>DM</sub>	800	А		
Maximum Power Dissipation	PD	300	W		
Derating factor		2	<b>W</b> /℃		
Single pulse avalanche energy (Note 5)	E <sub>AS</sub>	1700	mJ		
Operating Junction and Storage Temperature Range	T <sub>J</sub> ,T <sub>STG</sub>	-55 To 175	°C		



(2) D







### **Thermal Characteristic**

0.5	°C/W
	0.5

### Electrical Characteristics (T<sub>C</sub>=25<sup>°</sup>C unless otherwise noted)

Parameter Symbol		Condition	Min	Тур	Max	Unit	
Off Characteristics							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250µA	85		-	V	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =85V,V <sub>GS</sub> =0V	-	-	1	μA	
Gate-Body Leakage Current	I <sub>GSS</sub>	$V_{GS}$ =±20V, $V_{DS}$ =0V	-	-	±100	nA	
On Characteristics (Note 3)							
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS}$ , $I_{D}=250\mu A$	2.5		4.5	V	
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	$V_{GS}$ =10V, I <sub>D</sub> =100A	-	-	2.8	mΩ	
Forward Transconductance	<b>g</b> fs	V <sub>DS</sub> =10V,I <sub>D</sub> =100A	-	90	-	S	
Dynamic Characteristics (Note4)	Dynamic Characteristics (Note4)						
Input Capacitance	Clss		-	11500	-	PF	
Output Capacitance	C <sub>oss</sub>	$V_{DS}$ =40V, $V_{GS}$ =0V,	-	2990	-	PF	
Reverse Transfer Capacitance	C <sub>rss</sub>	F=1.0MHZ	-	105	-	PF	
Switching Characteristics (Note 4)							
Turn-on Delay Time	t <sub>d(on)</sub>		-	28	-	nS	
Turn-on Rise Time	tr	V <sub>DD</sub> =40V,I <sub>D</sub> =100A	-	73	-	nS	
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GS}$ =10V, $R_{G}$ =1.6 $\Omega$	-	86	-	nS	
Turn-Off Fall Time	t <sub>f</sub>		-	33	-	nS	
Total Gate Charge	Qg	N/ 40)/1 400A	-	165		nC	
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS} = 40V, I_D = 100A,$	-	56		nC	
Gate-Drain Charge	Q <sub>gd</sub>	V <sub>GS</sub> =10V	-	35		nC	
Drain-Source Diode Characteristics							
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	$V_{GS}$ =0V,I <sub>F</sub> = I <sub>S</sub>	-		1.2	V	
Diode Forward Current (Note 2)	I <sub>S</sub>		-	-	250	Α	
Reverse Recovery Time	t <sub>rr</sub>	$T_J$ = 25°C, $I_F$ = $I_S$	-	115		nS	
Reverse Recovery Charge	Qrr	di/dt = 100A/µs <sup>(Note3)</sup>	-	320		nC	

#### Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2. Surface Mounted on FR4 Board, t  $\leq$  10 sec.

3. Pulse Test: Pulse Width  $\leq$  300µs, Duty Cycle  $\leq$  2%.

4. Guaranteed by design, not subject to production

5. EAS condition : Tj=25  $^\circ C$  ,V\_{DD}=42.5V,V\_G=10V,L=0.5mH,Rg=25\Omega



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### Test Circuit 1) E<sub>AS</sub> test Circuit



### 2) Gate charge test Circuit



3) Switch Time Test Circuit





NCEP85T25D







Figure 4 Rdson-JunctionTemperature





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Pb Free Product



## TO-263-2L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min.	Max.	Min.	Max.	
А	4.470	4.670	0.176	0.184	
A1	0.000	0.150	0.000	0.006	
В	1.170	1.370	0.046	0.054	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
С	0.310	0.530	0.012	0.021	
c1	1.170	1.370	0.046	0.054	
D	10.010	10.310	0.394	0.406	
E	8.500	8.900	0.335	0.350	
e	2.540 TYP.		0.100 TYP.		
e1	4.980	5.180	0.196	0.204	
L	15.050	15.450	0.593	0.608	
L1	5.080	5.480	0.200	0.216	
L2	2.340	2.740	0.092	0.108	
L3	1.300	1.700	0.051	0.067	
V	5.600	REF	0.220	REF	







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